

[Accurate junction capacitance model for high-speed circuit simulator]

Abstract of Disclosure

A method for modeling junction capacitance of the MOSFET transistor is proposed and implemented for high-speed circuit simulator. A region-based value of the capacitance of MOSFET is proposed, and its regional capacitance value model is more accurate and takes less computation time than the conventional bias independent average capacitance model.

Figures

Figure 1: A vertical strip of text containing a list of names and dates, likely a table of contents or index. The text is rotated 90 degrees counter-clockwise.